Amendments to the Specification:

Please replace the eighth full paragraph on page 1 (page 1, line 32-page 2, line 3) with the following:

Generally, since the MLP has the depth of about 0.2 mm and is very thin, its shape is formed using an etching method. However, in a case where a bottom surface of the thin MLF is exposed in a state not encapsulated by an EMC, attachment strength between the EMC and the MLF ~~30~~ after a molding process, that is, molderability is reduced. In order to prevent the above problem, the pattern of the MLF is formed using a half-etching method.

Please replace the third full paragraph on page 4 (page 4, lines 11-29) with the following:

Here, the oblique etching method proceeds as follows. First, a photoresist is coated on upper and lower surfaces of a leadframe member, and then, an etching solution is injected therein, thereby obtaining an oblique etched MLF pattern. Here, the size of the oblique etched pattern of the bottom surface of the MLF is ~~lightly~~ slightly greater than that of the oblique etched pattern of the upper surface. In the oblique etching method, attachment strength in an up-and-down direction between the MLF and an EMC is improved, compared to the general etched leadframe which is etched in a vertical direction. Further, in the MLF using the existing half-etching method, in order to make the MLF into an elaborate shape, an etching solution or an etching method used in the upper surface of the MLF must be different from those used in the bottom surface. However, the above-described difficult process of the existing half-etching method is not required in the oblique etching method. That is, the oblique etching method can be performed using simple processes, which is applied in the vertical-etching method. Thus, the manufacturing cost of the MLF formed using the oblique etching method is more inexpensive than that of the MLF formed using the

half-etching method, and the yield of the MLF becomes higher. Preferably, the size of the oblique etching portion in the bottom surface of the MLF is greater than that of the upper surface by about 1-10%. The oblique etching portion in the bottom surface may be greater beyond the above range, as needed.

Please replace the sixth full paragraph on page 5 (page 5, line 32-page 6, line 13) with the following:

The MLP 110 includes an MLF having a die pad 116 on which a semiconductor chip 120 is mounted, leads 114 formed along outer sides of the die pad 116, and tie bars 132 for supporting four corners of the die pad 116. Here, the die pad 116, the leads 114, and tie bars 132 are oblique-etched as described above. A plurality of dimples 134 are formed on the leads 114, four edges of the die pad 116, and the tie bars 132 to improve the attachment strength between the MLF and an EMC ~~120~~ 112. The semiconductor chip 120 is mounted on the die pad 116 of the MLF via adhesive means 118. The semiconductor ~~chi~~ chip 120 is connected electrically to the leads 114 through wires 122. A reference numeral 124 represents a ground bonding wire for directly connecting the semiconductor chip 120 to the die pad 116. The semiconductor ~~chip1 20~~ chip 120, the wires 122 and 124, and the MLF, except a bottom surface thereof, are encapsulated by an EMC ~~120~~ 112. A solder 126 is plated in the exposed leads 114 and the exposed bottom surface of the die pad 116, and a solder 138 is plated in side surfaces of the leads 114 using holes for firm solder connection (refer to the reference number 136 of FIG. 6). Thus, when the MLP 110 is mounted on the PCB, the attachment strength between the MLP 110 and the PCB increases.

Please replace the fifth full paragraph on page 6 (page 6, lines 22-26) with the following:

_____While the present invention has been particularly shown and described with reference to preferred embodiments thereof, it will be understood by those of ordinary skill in the art that various changes in form and details may be made therein without departing from the spirit and scope of the present invention as defined by the appended claims.